Title (en)
METHOD FOR PRODUCING A THIN LAYER PHOTOVOLTAIC SYSTEM AND THIN LAYER PHOTOVOLTAIC SYSTEM

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES DÜNNSCHICHT-PHOTOVOLTAIK-SYSTEMS UND DÜNNSCHICHT-PHOTOVOLTAIK-SYSTEM

Title (fr)
PROCÉDÉ DE FABRICATION D'UN SYSTÈME PHOTOVOLTAÏQUE EN COUCHES MINCES ET SYSTÈME PHOTOVOLTAÏQUE EN COUCHES MINCES

Publication
EP 2404326 A2 20120111 (DE)

Application
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Abstract (en)
[origin: EP2216832A2] The method involves using a flat metal chalcogenide compound semiconductor layer as an absorber for sunlight and a metal layer applied to the metal chalcogenide compound semiconductor layer. The metal chalcogenide compound semiconductor layer and the metal layer form a Schottky contact at their contact surface. The metal chalcogenide compound semiconductor layer is manufactured by applying a dispersion containing nano-scale particles with a diameter of about 3 to 30 nanometer on a transparent substrate material.

IPC 8 full level
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